

Appendixes A

The following is the list of references for **Figure. 1 (f)**.

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- [S14] He Z, Zhang X, Pieshkov T, et al. Reduced trap state density in AlGa_N/GaN HEMTs with lowtemperature CVD-grown BN gate dielectric. *Appl. Phys. Lett.*, 2024, 125, 042106.
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